Supporting Information

Low band-gap copolymer composed of thienyl substituted anthracene and diketopyrrolopyrrole compatible with multiple electron acceptors for high efficiency polymer solar cells

Jae Woong Jung^a and Won Ho Jo*^a

^aDepartment of Materials Science and Engineering, Seoul National University, 1 Gwanak-ro, Gwanak-gu, San 56–1, Seoul 151–744, Korea

Characterization

1H NMR spectra were obtained from Bruker Avance 300MHz NMR spectrometer with deuterated chloroform as a solvent. Size exclusion chromatography was performed at room temperature on Agilent 1200 GPC System (eluted with CHCl₃). The molecular weights were calculated according to relative calibration with polystyrene standards. UV-Vis absorption spectra were measured with a Lambda 25 (Perkin Elmer) spectrometer. Cyclic voltammetry experiments were carried out on a potentiostat/galvanostat (VMP3, Biologic) in an electrolyte solution of 0.1 M tetrabutylammonium hexafluorophosphate in acetonitrile using gold electrodes as a counter and a working electrode, respectively, and silver/silver ion (Ag in 0.1 M AgNO₃ solution) was used as a reference electrode. The thin film morphology was observed by transmission electron microscopy (TEM) (JEM1010) operating at 80 kV of acceleration voltage. The crystallinities of the films were investigated by X-ray diffractometer (M18XHF-SRA). To characterize charge transport characteristics of the copolymers, thin film transistors (bottom-gate top-contact device geometry) were fabricated. On the heavily ndoped SiO₂/Si substrate, the spin-coated films (thickness of 50 nm) of PTATDPP or PTAFDPP were coated from chloroform solution. Surface of the substrate was treated by octadecyltrichlorosilane to make hydrophobic dielectric surface. Au was then thermally evaporated (60 nm) as source and drain electrodes with channel width and length of 1500 µm and 30 µm, respectively. All the devices were fabricated in this study were clearly isolated to

achieve negligible gate leakage current. All the field effect mobilities were extracted in the saturation regime using the relationship μ sat = $(2 \cdot I_{DS} \cdot L)/(W \cdot C(V_G - V_{th})^2)$, where I_{DS} is saturation drain current, C is capacitance of SiO₂ dielectric, V_G is gate bias, and V_{th} is threshold voltage. The device performance was evaluated under N₂ atmosphere using 4200-SCS semiconductor characterization system.



Figure S1. Photoluminescence spectra of PTATDPP and PTAFDPP films on glass substrates (excited at 600 nm).



Figure S2. Current density–voltage curves of the PSC devices based on PTATDPP:PC₇₁BM blend with different blend ratios (left) and PTAFDPP:PC₇₁BM blend with different blend ratios (right) under the illumination of AM 1.5G, 100 mW/cm².



Fig. S3. Incident photon to current efficiencies of PSC devices made of PTATDPP:PC₇₁BM blend and PTAFDPP:PC₇₁BM blend films.



Fig. S4. (a) Height and (b) phase images of PTATDPP:di-PBI observed from AFM.



Fig. S5. TEM image of PTATDPP:di-PBI blend film.



Fig. S6. 1H NMR spectrum of M1.



Fig. S7. 1H NMR spectrum of M2.



Fig. S8. 1H NMR spectrum of M3.

Table	S1.	Photovolatic	parameters	of PSC	devices	based	on	PTATDPP:PC ₇₁ BM	blend
PTAFDPP:PC ₇₁ BM blend with different blend ratios									

Polymer	Ratio	Voc	J _{SC}	FF	РСЕ	
i orymer	to :PC ₇₁ BM	(V)	(mA/cm ²)		(%) ^a	
	1.1	0.80	11.0	0.62	5.42	
	1.1	(0.80 ± 0.01)	(10.6 ± 0.4)	(0.60 ± 0.02)	(5.11 ± 0.30)	
	1:1.5	0.81	11.1	0.61	5.47	
		(0.80 ± 0.01)	(10.8 ± 0.3)	(0.60 ± 0.01)	(5.25 ± 0.21)	
riaidfr	1:2	0.80	12.3	0.68	6.69	
		(0.80 ± 0.01)	(11.4 ± 0.9)	(0.65 ± 0.03)	(6.45 ± 0.24)	
	1:3	0.81	11.0	0.63	6.00	
		(0.80 ± 0.01)	(10.2 ± 0.7)	(0.59 ± 0.03)	(5.60 ± 0.40)	
	1.1	0.71	10.0	0.59	4.14	
	1.1	(0.71 ± 0.01)	(9.4 ± 0.6)	(0.57 ± 0.02)	(3.88 ± 0.25)	
	1.1.5	0.73	11.0	0.60	4.71	
ΔΤΑΓΊΔΟ	1.1.3	(0.72 ± 0.01)	(10.6 ± 0.3)	(0.57 ± 0.02)	(4.50 ± 0.21)	
ΓΙΑΓDΓΓ	1.2	0.76	11.2	0.59	5.02	
	1.2	(0.75 ± 0.01)	(10.1 ± 1.1)	(0.57 ± 0.02)	(4.68 ± 0.34)	
	1.2	0.77	10.1	0.59	4.59	
	1.3	(0.76 ± 0.01)	(9.6 ± 0.4)	(0.55 ± 0.04)	(4.43 ± 0.16)	

^aMore than 20 devices were fabricated in each condition.

Dolymon	Ratio to	Device	V _{oc}	J _{SC}	FF	РСЕ
rorymer	PC ₇₁ BM	architecture	(V)	(mA/cm ²)		(%) ^a
	1.2	conventional	0.80	12.3	0.68	6.69
	1.2		(0.80 ± 0.01)	(11.4 ± 0.9)	(0.65 ± 0.03)	(6.45 ± 0.24)
PIAIDPP		inverted	0.80	13.1	0.67	7.02
			(0.80 ± 0.01)	(12.5 ± 0.6)	(0.64 ± 0.03)	(6.75 ± 0.27)
	1:2	conventional	0.76	11.2	0.59	5.02
			(0.75 ± 0.01)	(10.1 ± 1.1)	(0.57 ± 0.02)	(4.68 ± 0.34)
ΓΙΑΓDΓΓ		inverted	0.75	11.4	0.61	5.22
			(0.75 ± 0.01)	(10.6 ± 0.5)	(0.57 ± 0.03)	(4.87 ± 0.35)

Table S2. Photovoltaic parameters of optimized devices based on PTATDPP and PTAFDPP.

^aMore than 20 devices were fabricated in each condition.

Reference

- L. Dou, J. Gao, E. Richard, J. You, C.-C. Chen, K. C. Cha, Y. He, G. Li and Y. Yang, J. Am. Chem. Soc., 2012, 134, 10071
- L. Dou, W.-H. Chang, J. Gao, C.-C. Chen, J. You, Y. Yang, *Adv. Mater.*, 2013, 25, 825